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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

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MDD95-08N1B

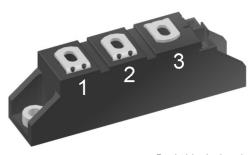
Standard Rectifier Module

V_{RRM}	<i>=</i> 2x	800 V
I _{fav}	=	120 A
V _F	=	1.13 V

Phase leg

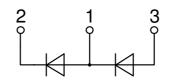
Part number

MDD95-08N1B



Backside: isolated **E**72873

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Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- · Very low leakage current

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- · Field supply for DC motors

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Height: 30 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office. Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

MDD95-08N1B

Rectifier					Rating	S	
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	repetitive reverse blocking voltage				900	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			800	V
I _R	reverse current	$V_{R} = 800 V$	$T_{VJ} = 25^{\circ}C$			200	μA
		$V_{R} = 800 V$	$T_{vJ} = 150^{\circ}C$			15	mA
V _F	forward voltage drop	I _F = 150 A	$T_{VJ} = 25^{\circ}C$			1.20	V
		I _F = 300 A				1.43	V
		$I_{F} = 150 \text{ A}$	T _{vJ} = 125°C			1.13	V
		$I_{F} = 300 \text{ A}$				1.46	V
FAV	average forward current	T _c = 100°C	$T_{VJ} = 150^{\circ}C$			120	A
I F(RMS)	RMS forward current	180° sine				180	Α
V _{F0}	threshold voltage $T_{y_{y_{z}}} = 150^{\circ}C$					0.75	۷
r _F	slope resistance } for power	loss calculation only				1.95	mΩ
R _{thJC}	thermal resistance junction to ca	ase				0.26	K/W
R _{thCH}	thermal resistance case to heatsink				0.20		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			481	W
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			2.80	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			3.03	kA
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150^{\circ}C$			2.38	kA
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			2.57	kA
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			39.2	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			38.1	kA²s
		t = 10 ms; (50 Hz), sine	$T_{vJ} = 150 ^{\circ}\text{C}$			28.3	kA²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			27.5	kA²s
C	junction capacitance	V _B = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		116		pF

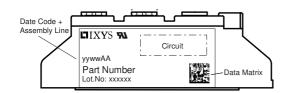
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MDD95-08N1B

Package	TO-240AA				F	Ratings	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
	RMS current	per terminal					200	Α
T _{vj}	virtual junction temperature				-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		125	°C
Weight						76		g
M _D	mounting torque				2.5		4	Nm
M _T	terminal torque				2.5		4	Nm
d _{Spp/App}	creenade distance on surfac	ce striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surrac	e striking distance through an	terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second			3600			V
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA		3000			V



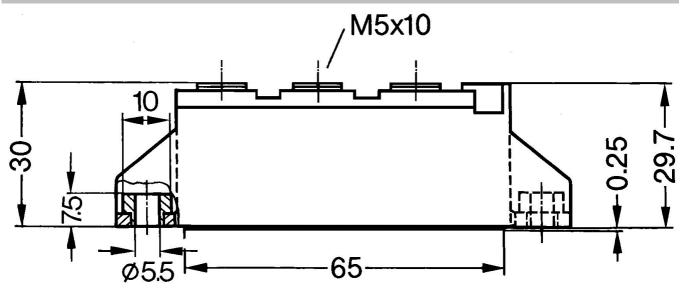
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDD95-08N1B	MDD95-08N1B	Box	36	453102

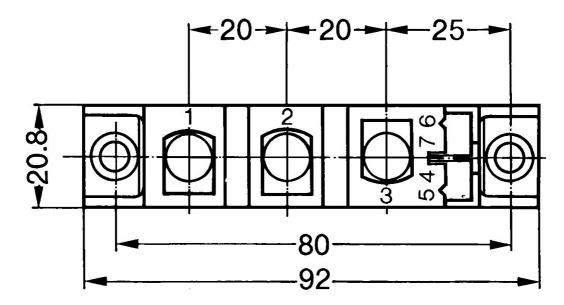
Similar Part	Package	Voltage class
MDD95-12N1B	TO-240AA	1200
MDD95-14N1B	TO-240AA	1400
MDD95-16N1B	TO-240AA	1600
MDD95-18N1B	TO-240AA	1800

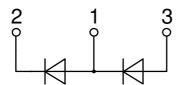
Equiva	lent Circuits for	Simulation	* on die level	T _{vj} = 150 °C
	- R _o -	Rectifier		
V _{0 max}	threshold voltage	0.75		V
$\mathbf{R}_{0 \max}$	slope resistance *	0.76		mΩ

 $\ensuremath{\mathsf{IXYS}}$ reserves the right to change limits, conditions and dimensions.

Outlines TO-240AA







200

Rectifier

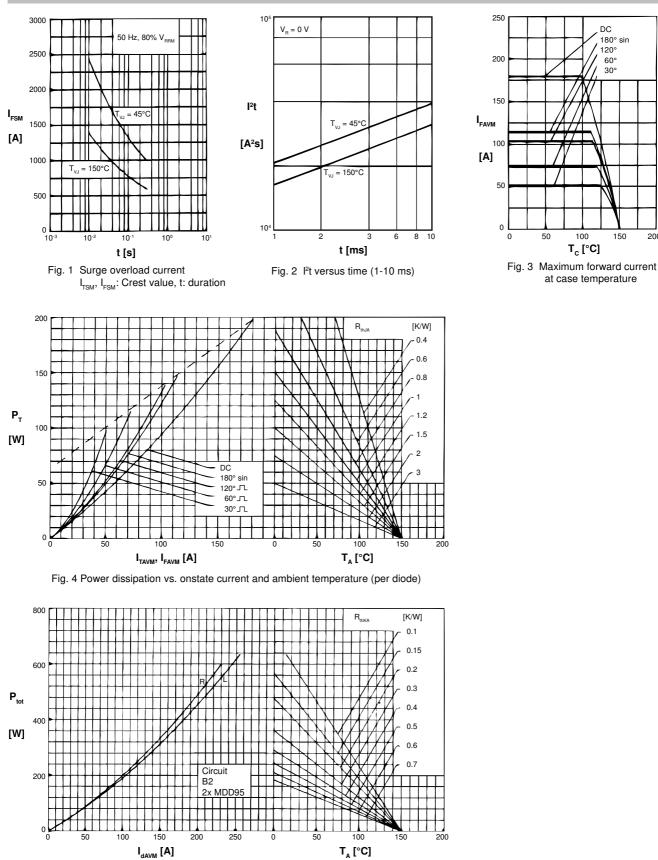
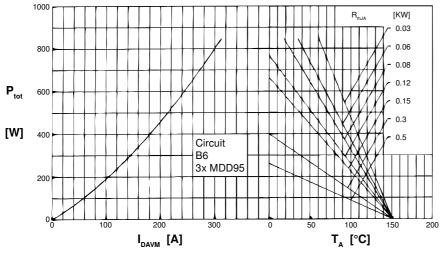


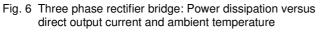
Fig. 6 Single phase rectifier bridge: Power dissipation versus direct output current and ambient temperature; R = resistive load, L = inductive load

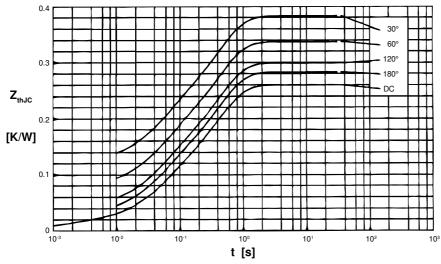
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MDD95-08N1B

Rectifier







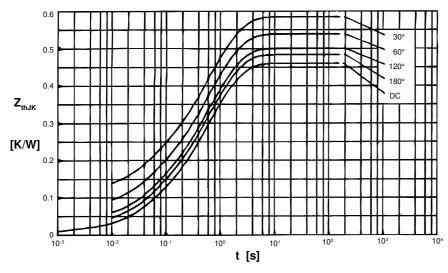
	- thJC			
DC	0.26			
180°	0.28			
120°	0.30			
60°	0.34			
30°	0.38			
Constants for Z_{thJC} calculation:				
i R _{thi} [K/W] t _i [s]				

 ${\rm R}_{\rm thJC}$ for various conduction angles d:

d R_{in in} [K/W]

i	R _{thi} [K/W]	t _i [s]
1	0.013	0.0012
2	0.072	0.0470
3	0.175	0.3940

Fig. 7 Transient thermal impedance junction to case (per diode)



$R_{_{thJK}}$ for v	arious cor	nduction angles d:
d	R _{thJK} [K/V	N]
DC	0.46	
180°	0.48	
120°	0.50	
60°	0.54	
30°	0.58	
Constant	s for Z _{thJK} (calculation:
i R _{thi} [K	K/W] t _i	[s]
1 0.0	13 0.0)012
0 00	70 00	1470

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1	0.013	0.0012
2	0.072	0.0470
3	0.175	0.3940
4	0.200	1.3200

Fig. 8 Transient thermal impedance junction to heatsink (per thyristor)

IXYS reserves the right to change limits, conditions and dimensions.